



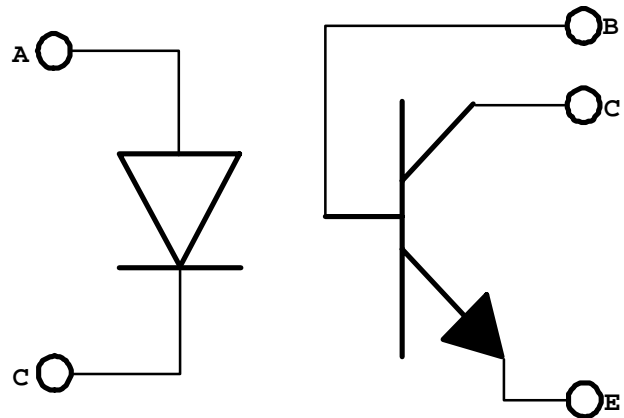
NPN Photo Transistor Hybrid Optocoupler

Features

- Small size
- Gold thick film bonding pads
- Custom input and output versions
- Low input current operation

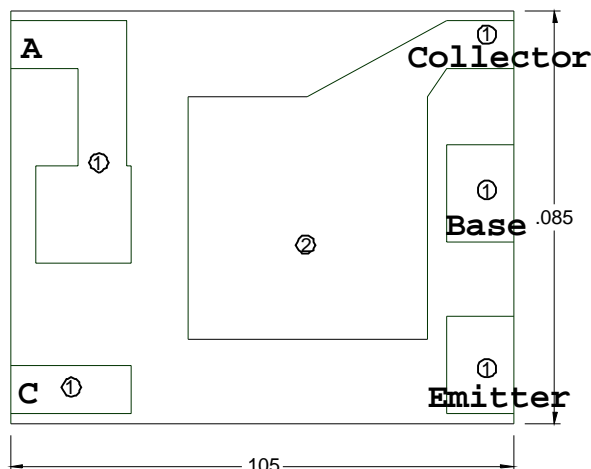
Applications

- Solid state relays
- Switching power supplies
- CMOS drivers
- Light meters



Electrical Characteristics @ 25°C

SYMBOL	CHARACTERISTIC	CONDITIONS	MIN	TYP	MAX	UNITS
CTR	Current Transfer Ratio	IF = 10 mA, VCE = 5.0 V	50	100		%
VCE(SAT)	Collector-Emitter Saturation Voltage	IF = 10 mA, IC = 1.0 mA		0.25		Volts
BVCEO	Collector-Emitter Voltage	IC = 100 uA	20			Volts
ICEO	Collector-Emitter Leakage Current	VCE = 20 V			100	nAmps
VF	Input Forward Voltage	IF = 10 mA	0.85	1.2	1.95	Volts
IR	Input Reverse Current	VR = 3.0 V			100	uAmps
T(on)	Turn-On Time	IF = 20 mA, VCE = 5 V, RL = 100 Ohms			30	usec



Notes:

1. Fritless gold over Pt-Au or Pd-Au metallization
2. Pt-Au or Pd-Au metallization

hybrid substrate size
 0.105 x 0.085 inch

wirebond contact size
 0.010 x 0.010 inch